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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 125664		APPLICATION NO. New U.S. National Stage of PCT/JP04/006003 <b>10/553754</b>	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANT Makoto IIDA			
				FILING DATE October 18, 2005			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS
Smm	1	JP A 2002-201093 w/abstr. & trans.	07/16/2002	JAPAN			
Smm	2	JP A 2000-001391 w/abstr. & trans.	01/07/2000	JAPAN			
Smm	3	JP A 09-263485 w/abstr. & trans.	10/07/1997	JAPAN			
Smm	4	JP A 11-147786 w/abstr. & trans.	06/02/1999	JAPAN			
Smm	5	JP A 2000-044388 w/abstr. & trans.	02/15/2000	JAPAN			
Smm	6	JP A 11-349394 w/abstr. & trans.	12/21/1999	JAPAN			
Smm	7	JP A 2002-057160 w/abstr. & trans.	02/22/2002	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
Smm	8	V.V. VORONOKOV; "The Mechanism of Swirl Defects Formation in Silicon"; Journal of Crystal Growth; Vol. 59; March 1982; pp. 625-643					
EXAMINER		<i>J. m. malek zadeh</i>				DATE CONSIDERED <i>03/14/2007</i>	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: October 18, 2005